NPN diffused silicon planar transistor

BSV 92

High speed saturated switch

The BSV 92 in an NPN planar epitaxial transistor designed specifically for high speed saturated switching applications.

ELECTRICAL CHARACTERISTICS
(T_A = 25°C unless otherwise noted)

Symbol	Characteristic and test conditions		Min.	Typ.	Max.	Unit
h_{FE}	DC Current Gain (5)					
	I_C = 1 mA	V_{CE} = 1V		85		
	I_C = 10 mA	V_{CE} = 0,35V	55	80		
	I_C = 10 mA	V_{CE} = 1V	70	95	120	
	I_C = 100 mA	V_{CE} = 1V	25	60		
h_{FE} (-55°C)	DC Current Gain (5)					
	I_C = 10 mA	V_{CE} = 0,35V	20			
V_{BE} sat	Base Saturation Voltage (5)					
	I_C = 10 mA	I_B = 1 mA	0.7	0.77	0.85	V
	I_C = 100 mA	I_B = 10 mA		1	1.5	V
V_{CE} sat	Collector Saturation Voltage (5)					
	I_C = 10 mA	I_B = 1 mA		0.14	0.20	V
	I_C = 100 mA	I_B = 10 mA		0.30	0.50	V
	I_C = 1 mA	I_B = 0.1 mA		0.16		V
I_{CES}	Collector Reverse Current					
	V_{CE} = 20V	V_{EB} = 0		5	200	nA
I_{CES} (150°C)	Collector Reverse Current					
	V_{CE} = 20V	V_{EB} = 0		5	70	μA
BV_{CES}	Collector to Emitter Breakdown Voltage					
	I_C = 10 μA	V_{EB} = 0	40			V
BV_{EBO}	Emitter to Base Breakdown Voltage					
	I_E = 10 μA	I_C = 0	5			V
LV_{CEO}	Collector to Emitter Sustaining Voltage (4 and 5)					
	I_C = 10 mA	I_B = 0	15			V
h_{fe}	High Freq. Current Gain (f = 100 MHz)					
	I_C = 10 mA	V_{CE} = 10V	5	6.5		
C_{TE}	Emitter Transition Capacitance					
	I_C = 0	V_{EB} = 0.5V		4		pF
C_{obo}	Base - Collector Capacitance					
	I_E = 0	V_{CB} = 5V		2	4	pF
τ_s	Charge Storage Time Constant					
	$I_C \sim I_{B1} \sim I_{B2} \sim$ 10 mA				13	ns
t_{on}	Turn On Time					
	$I_C \sim$ 10 mA	$I_{B1} \sim$ 3 mA			12	ns
t_{off}	Turn Off Time					
	$I_C \sim$ 10 mA	$I_{B1} \sim$ 3 mA $I_{B2} \sim$ 1.5 mA			18	ns
V_{CE} sat (125°C)	I_C = 10 mA	I_B = 1 mA			0.3	V
V_{BE} sat (-55 to 125°C)	I_C = 10 mA	I_B = 1 mA	0,55		1.05	V
h_{FE}	I_C = 30 mA	V_{CE} = 1V	50	75		

ABSOLUTE MAXIMUM RATINGS (1)
(T_A = 25°C unless otherwise noted)

Voltages

Collector to Emitter (4)	V_{CEO}	15 V
Collector to Emitter	V_{CES}	40 V
Emitter to Base	V_{EBO}	5 V

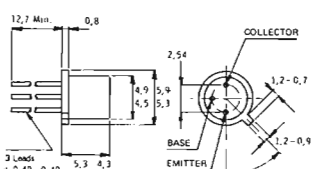
Temperatures

Storage Temperature	T_{STG}	-55°C to 200°C
Junction Temperature	T_J	200°C
Lead Temperature (Soldering 10 sec.)	T_L	260°C

Power (2 - 3)

Dissipation at 25°C Case Temperature	P_D	1 W
Dissipation at 25°C Ambient Temperature	P_D	0.36 W

PHYSICAL DIMENSIONS
Similar to Jedec TO-18



Note - All dimensions are in mm.

NOTES:

(1) These ratings are limiting values above which the serviceability of any individual semiconductor device may be impaired.
(2) Those are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.
(3) These ratings give a maximum junction temperature of 200°C and junction - to - case thermal resistance of 175°C/W (derating factor of 5.7 mW/°C); junction - to - ambient thermal resistance of 486°C/W (derating factor of 2.1 mW/°C).
(4) These ratings refer to a high - current point where collector - to - emitter voltage is lowest. For more information send for SGS - AR 5.
(5) Measured under pulse conditions: pulse length = 300 μsec; duty cycle = 1%.